



2SK3746

N-Channel Power MOSFET 1500V, 2A, 13Ω, TO-3P-3L

ON Semiconductor®

<http://onsemi.com>

Features

- Low ON-resistance, low input capacitance, ultrahigh-speed switching
- High reliability (Adoption of HVP process)
- Avalanche resistance guarantee

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		1500	V
Gate-to-Source Voltage	V _{GSS}		±20	V
Drain Current (DC)	I _D		2	A
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	4	A
Allowable Power Dissipation	P _D		2.5	W
		T _C =25°C	110	W
Channel Temperature	T _{ch}		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C
Avalanche Energy (Single Pulse) *1	E _{AS}		41	mJ
Avalanche Current *2	I _{AV}		2	A

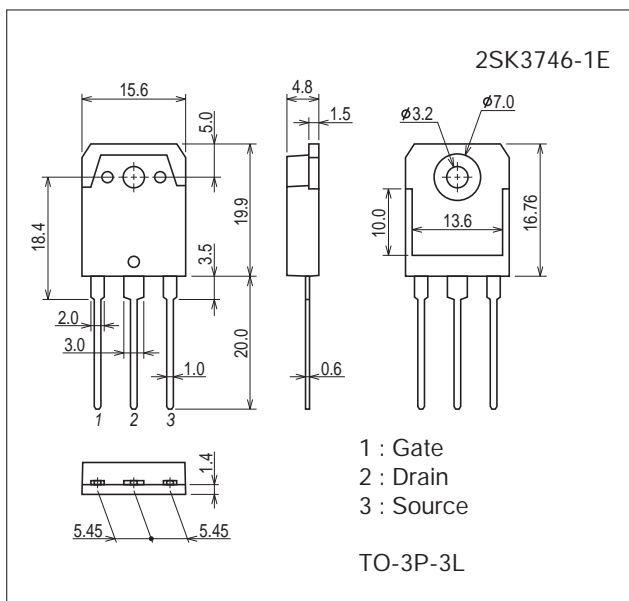
*1 V_{DD}=50V, L=20mH, I_{AV}=2A (Fig.1)

*2 L≤20mH, single pulse

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Package Dimensions

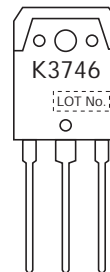
unit : mm (typ)
7539-002



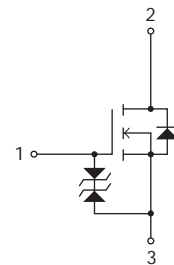
Product & Package Information

- Package : TO-3P-3L
- JEITA, JEDEC : SC-65, TO-247, SOT-199
- Minimum Packing Quantity : 30 pcs./magazine

Marking



Electrical Connection



Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	1500			V
Zero-Gate Voltage Drain Current	IDSS	VDS=1200V, VGS=0V			100	μA
Gate-to-Source Leakage Current	IGSS	VGS=16V, VDS=0V			±10	μA
Cutoff Voltage	VGS(off)	VDS=10V, ID=1mA	2.5		3.5	V
Forward Transfer Admittance	yfs	VDS=20V, ID=1A	0.7	1.4		S
Static Drain-to-Source On-State Resistance	RDS(on)	ID=1A, VGS=10V		10	13	Ω
Input Capacitance	Ciss	VDS=30V, f=1MHz		380		pF
Output Capacitance	Coss			70		pF
Reverse Transfer Capacitance	Crss			40		pF
Turn-ON Delay Time	td(on)	See Fig.2		12		ns
Rise Time	tr			37		ns
Turn-OFF Delay Time	td(off)			152		ns
Fall Time	tf			59		ns
Total Gate Charge	Qg	VDS=200V, VGS=10V, ID=2A		37.5		nC
Gate-to-Source Charge	Qgs			2.7		nC
Gate-to-Drain "Miller" Charge	Qgd			20		nC
Diode Forward Voltage	VSD	IS=2A, VGS=0V		0.88	1.2	V

Fig.1 Avalanche Resistance Test Circuit

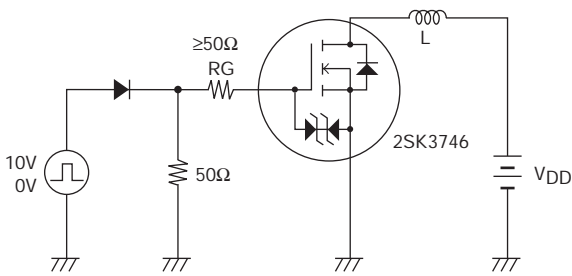
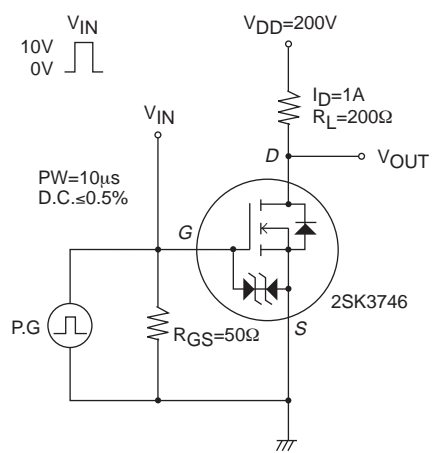
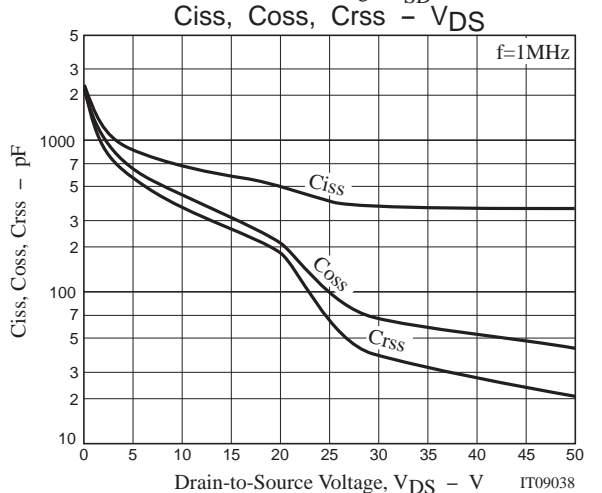
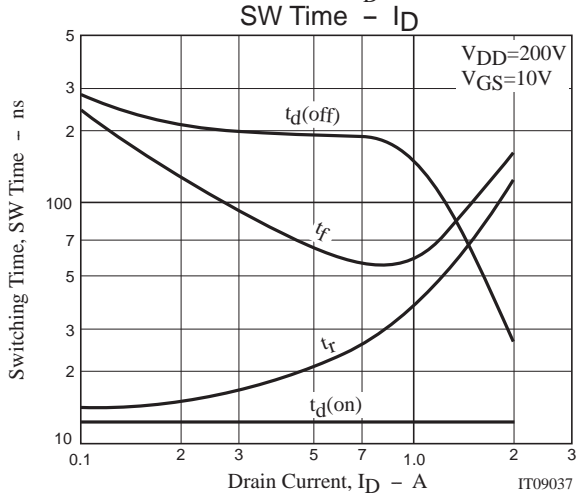
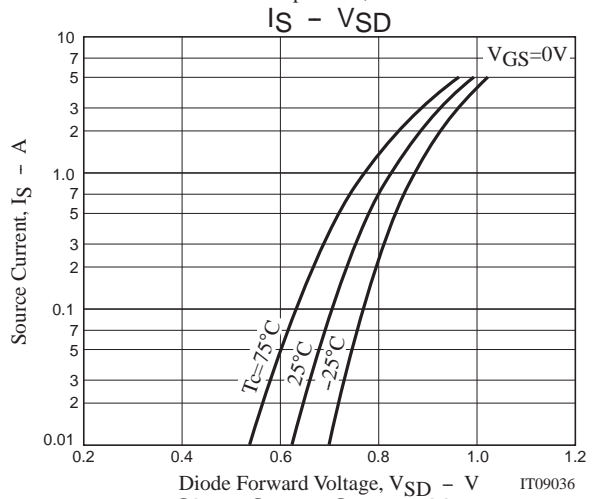
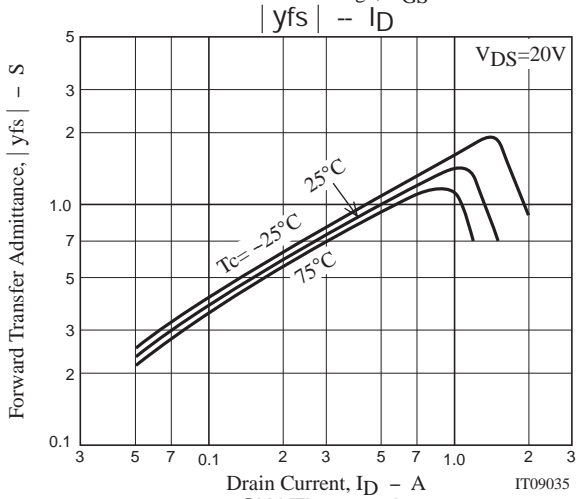
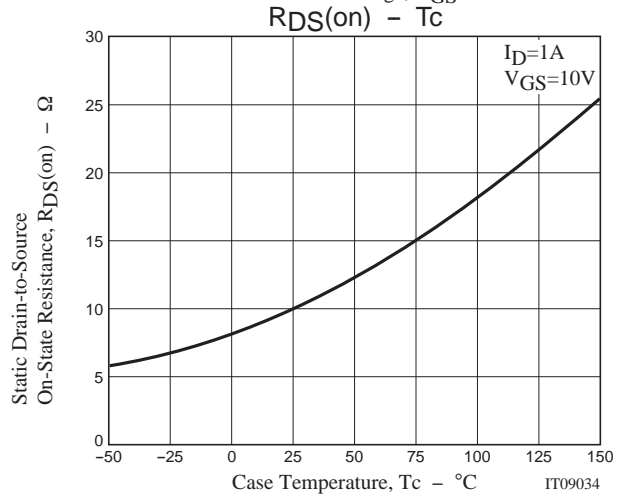
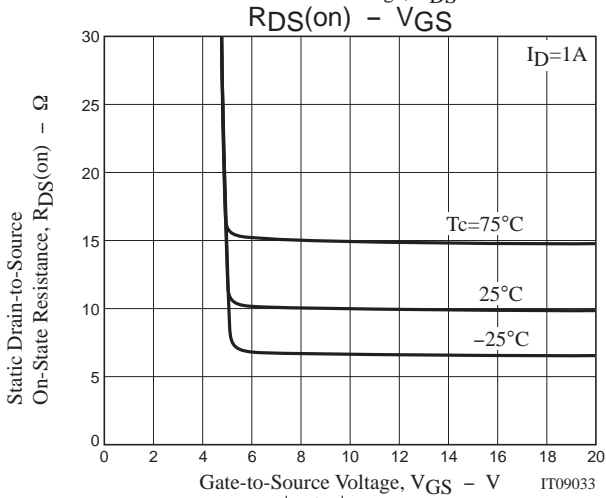
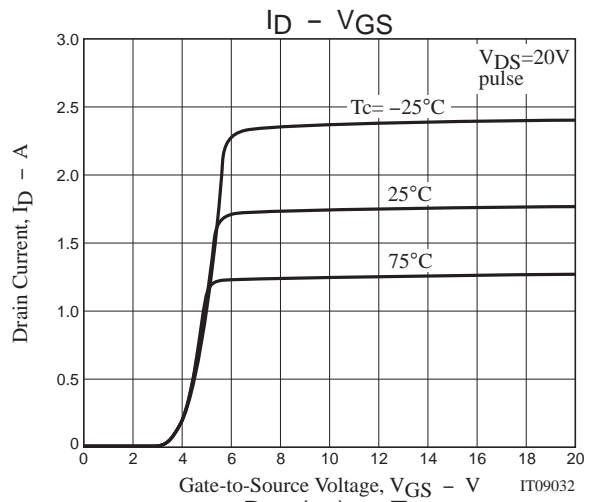
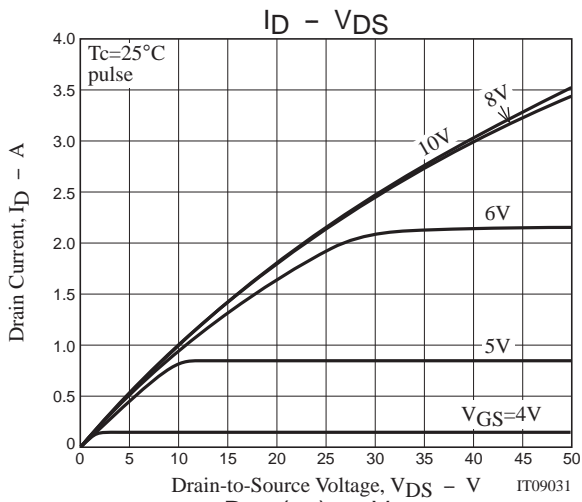


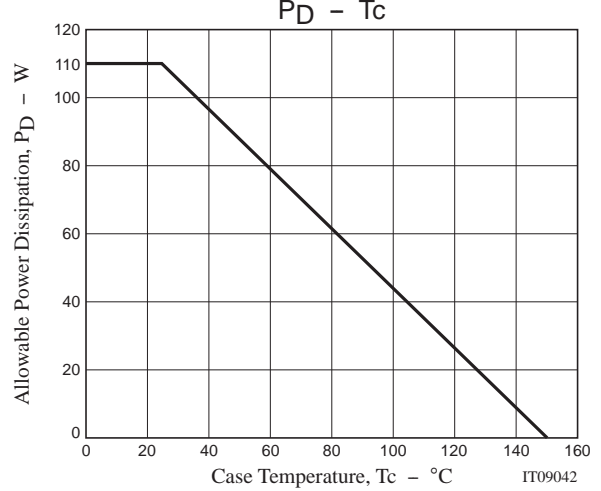
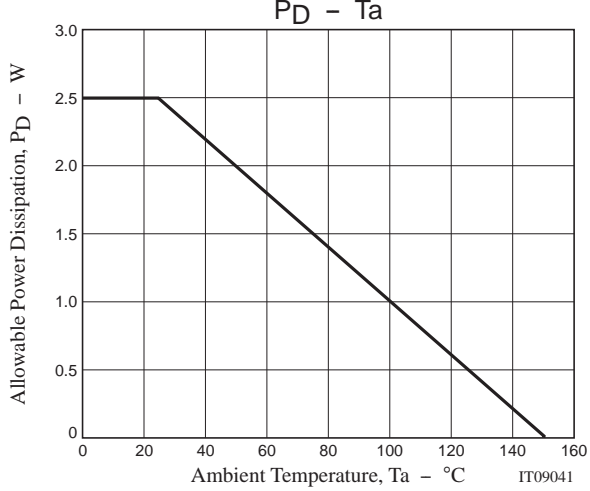
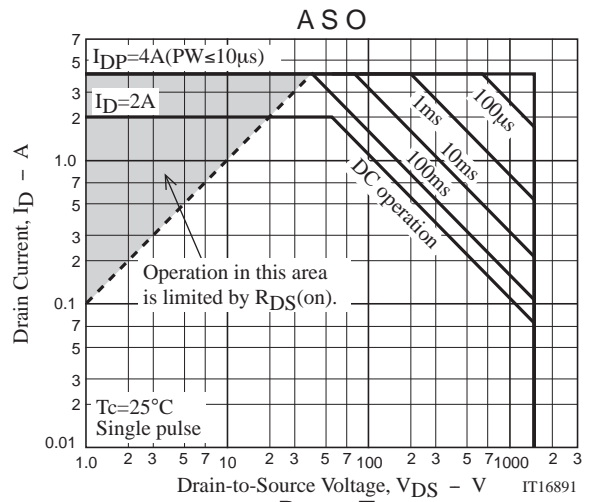
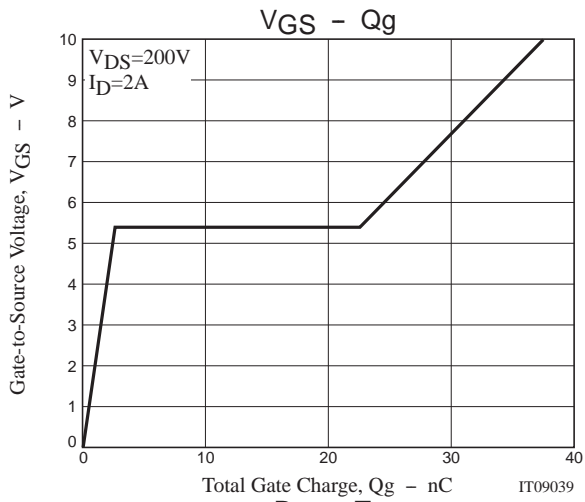
Fig.2 Switching Time Test Circuit



Ordering Information

Device	Package	Shipping	memo
2SK3746-1E	TO-3P-3L	30pcs./magazine	Pb Free





Magazine Specification

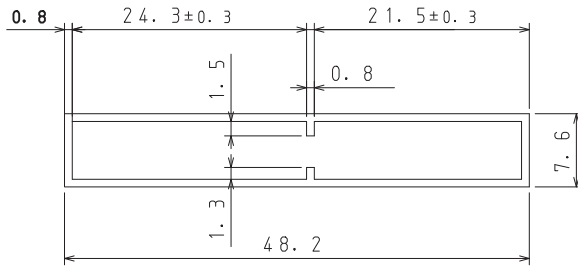
2SK3746-1E

1. Packing Format

Package Name	Maximum Number of devices contained (pcs)			Packing format	
	Magazine	Inner box	Outer box	Inner BOX	Outer BOX
TO-3P-3L	30	450	1800	SPD-0V0001 15 magazines contained Dimensions:mm (external) 568×150×55	SPD-LV0010 4 inner boxes contained Dimensions:mm (external) 590×225×178

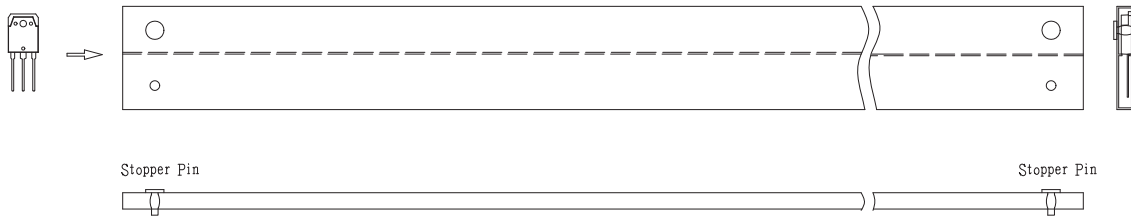
2. Magazine dimensions

(unit:mm)



Tolerance=±0.2mm
 Thickness=0.8±0.2mm
 Length =508.0±1mm
 Material =PVC or PET
 (Antistatic treatment)

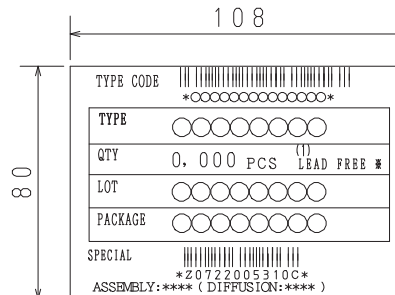
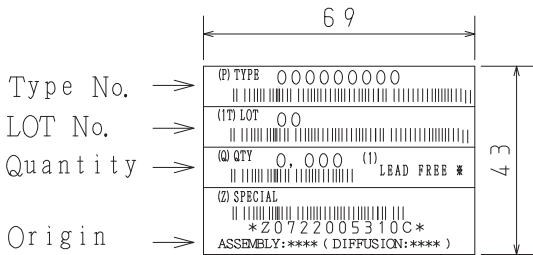
3. Storage method to magazine



4. Inner box label (unit:mm)

5. Outer box label (unit:mm)

It is a label at the time of factory shipments.
 The form of a label may change in physical distribution process.



NOTE (1)

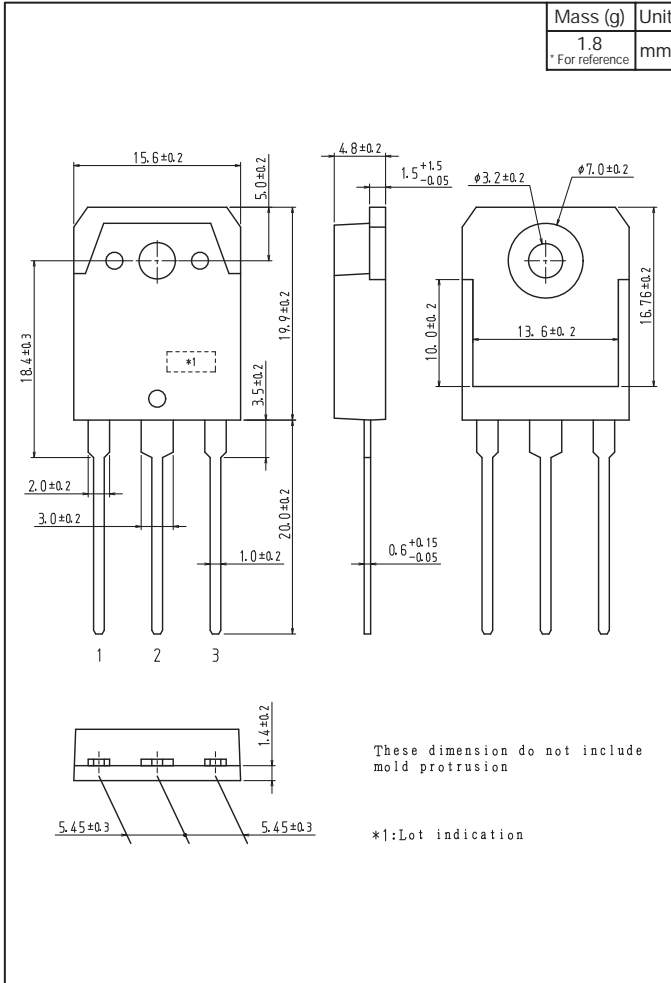
The LEAD FREE * description shows that the surface treatment of the terminal is lead free,

Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A

Outline Drawing

2SK3746-1E

Mass (g)	Unit
1.8	mm
* For reference	



Note on usage : Since the 2SK3746 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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